

Please add the following claims:

50. A process for forming layers in electronic devices comprising the steps of:
providing a reaction chamber;
placing a semiconductor wafer in said reaction chamber;
heating said semiconductor wafer with a thermal heating device placed adjacent to said wafer;
pulsing a precursor fluid into said reaction chamber, said precursor fluid forming a solid layer on said semiconductor wafer, wherein said solid layer comprises a material selected from the group consisting of tungsten, tungsten nitride, tantalum nitride, titanium nitride, copper, aluminum, ruthenium oxide, iridium oxide, and silver; and
thereafter exposing said solid layer to light energy in said reaction chamber;
wherein said precursor fluid is substantially exhausted and removed from said reaction chamber and said solid layer is exposed to said light energy in between each pulse of said precursor fluid.

51. A process for forming layers in electronic devices comprising the steps of:
providing a reaction chamber;
placing a semiconductor wafer in said reaction chamber;
heating said semiconductor wafer with a thermal heating device placed adjacent to said wafer;
pulsing a precursor fluid into said reaction chamber, said precursor fluid forming a solid layer on said semiconductor wafer, wherein said solid layer comprises a material selected from the group consisting of zirconium oxide, aluminum oxide, a nitride, barium strontium titanate and a silicate; and
thereafter exposing said solid layer to light energy in said reaction chamber;